

# Three quadrant triacs high commutation

# BTA204X series B and C

## GENERAL DESCRIPTION

Passivated high commutation triacs in a plastic full pack envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commute the full rated rms current at the maximum rated junction temperature without the aid of a snubber.

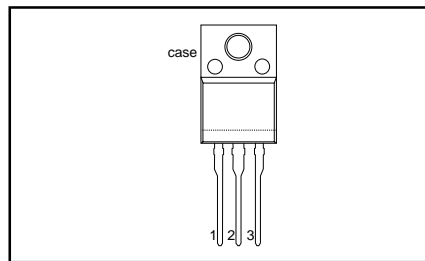
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
		500B 500C	600B 600C	800B 800C	
$V_{DRM}$	Repetitive peak off-state voltages	500	600	800	V
$I_{T(RMS)}$	RMS on-state current	4	4	4	A
$I_{TSM}$	Non-repetitive peak on-state current	25	25	25	A

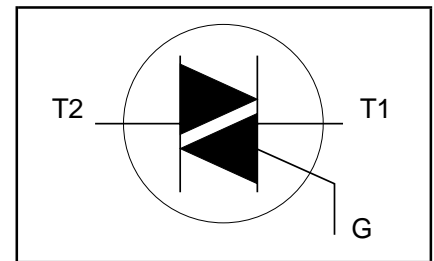
## PINNING - SOT186A

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500 500 <sup>1</sup>	-600 600 <sup>1</sup>	-800 800	
$V_{DRM}$	Repetitive peak off-state voltages		-				V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{hs} \leq 92^\circ\text{C}$	-	4			A
$I_{TSM}$	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ\text{C}$ prior to surge	-	25			A
		$t = 20\text{ ms}$	-	27			A
		$t = 16.7\text{ ms}$	-	3.1			A <sup>2</sup> s
$I^2t$	$I^2t$ for fusing	$t = 10\text{ ms}$	-	100			A/μs
$dl_T/dt$	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 6\text{ A}; I_G = 0.2\text{ A}; dl_G/dt = 0.2\text{ A}/\mu\text{s}$	-				
$I_{GM}$	Peak gate current		-	2			A
$V_{GM}$	Peak gate voltage		-	5			V
$P_{GM}$	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
$T_{stg}$	Storage temperature		-40	150			°C
$T_j$	Operating junction temperature		-	125			°C

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/μs.

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### ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{isol}$	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50\text{-}60\text{ Hz}$ ; sinusoidal waveform; $R.H. \leq 65\%$ ; clean and dustfree	-		2500	V
$C_{isol}$	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	full or half cycle with heatsink compound	-	-	5.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	without heatsink compound in free air	-	55	7.2	K/W

### STATIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.		UNIT
					...B	...C	
$I_{GT}$	Gate trigger current <sup>2</sup>	<b>BTA204X-</b>					
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$					
		T2+ G+	-	-	50	35	mA
$I_L$	Latching current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$					
		T2+ G+	-	-	50	35	mA
		T2- G-	-	-	50	35	mA
$I_H$	Holding current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$					
		T2+ G+	-	-	30	20	mA
		T2- G-	-	-	45	30	mA
$V_T$	On-state voltage	$I_T = 5\text{ A}$	-	1.4	1.7		V
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$	-	0.7	1.5		V
$V_{GT}$	Gate trigger voltage	$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ;	0.25	0.4	-		V
		$T_j = 125\text{ }^{\circ}\text{C}$					
$I_D$	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^{\circ}\text{C}$	-	0.1	0.5		mA

### DYNAMIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		TYP.	UNIT
			...B	...C		
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; exponential waveform; gate open circuit	1000	1000	-	V/ $\mu\text{s}$
$dl_{com}/dt$	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; gate open circuit	6	3	-	A/ms
$t_{gt}$	Gate controlled turn-on time	$I_{TM} = 12\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1\text{ A}$ ; $dl_G/dt = 5\text{ A}/\mu\text{s}$	-	-	2	$\mu\text{s}$

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

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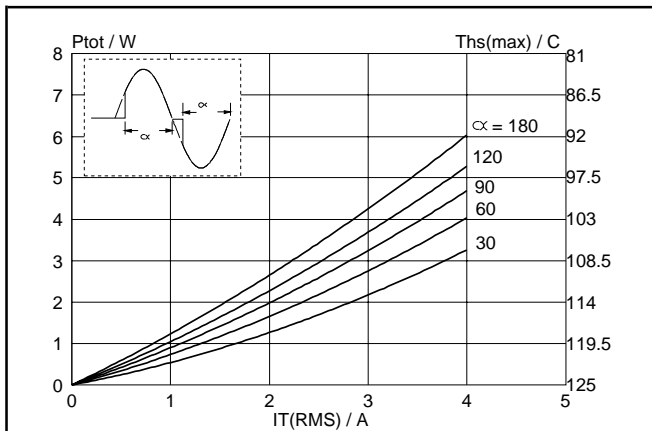


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha =$  conduction angle.

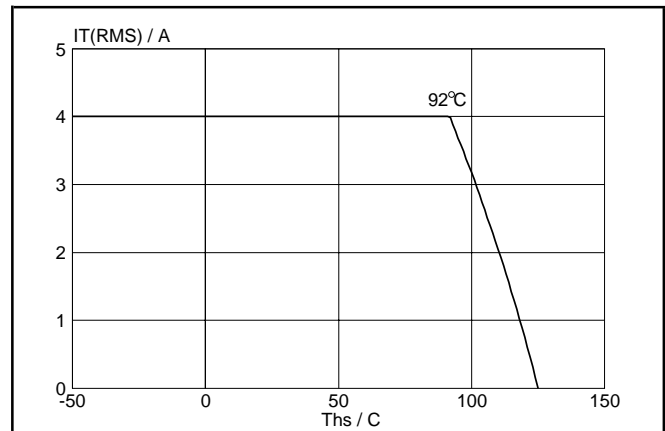


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus heatsink temperature  $T_{hs}$ .



Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20ms$ .

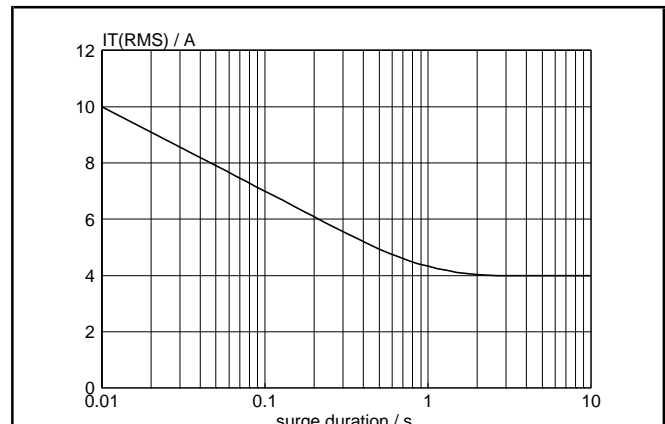


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50$  Hz;  $T_{hs} \leq 92$  C.



Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50$  Hz.

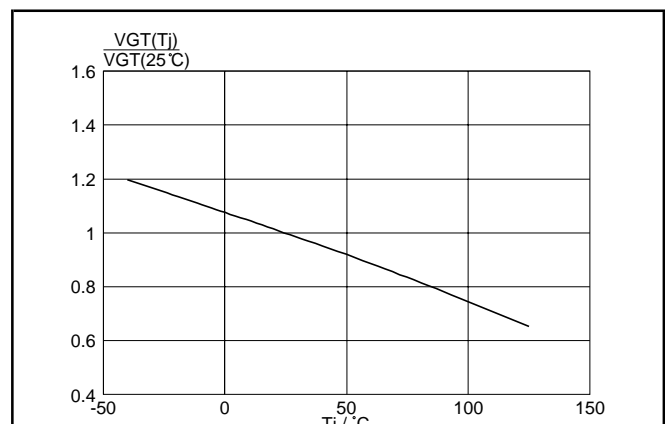
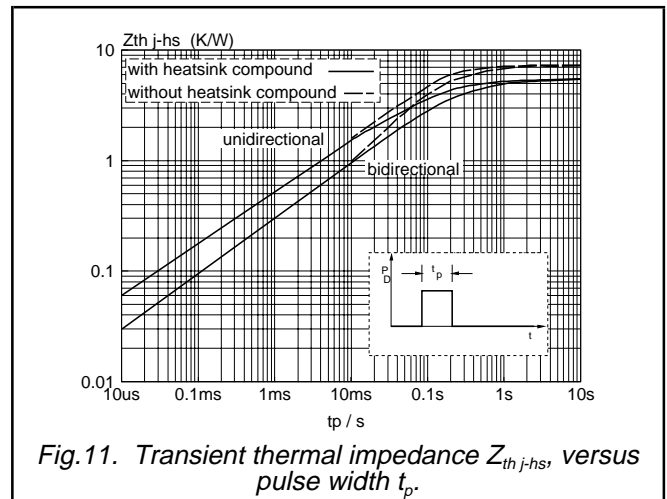
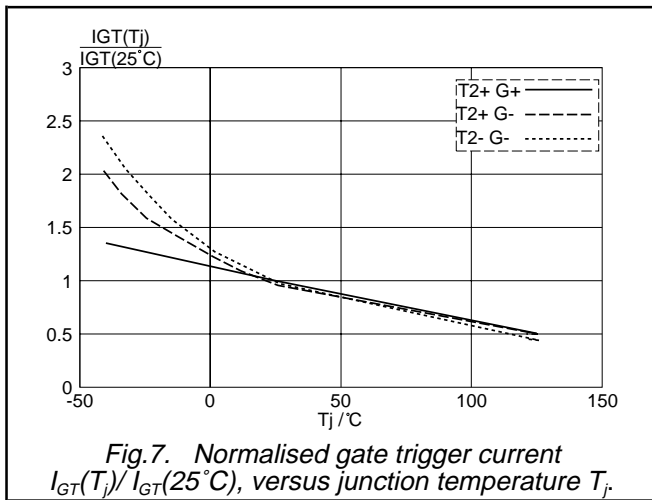


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^\circ C)$ , versus junction temperature  $T_j$ .

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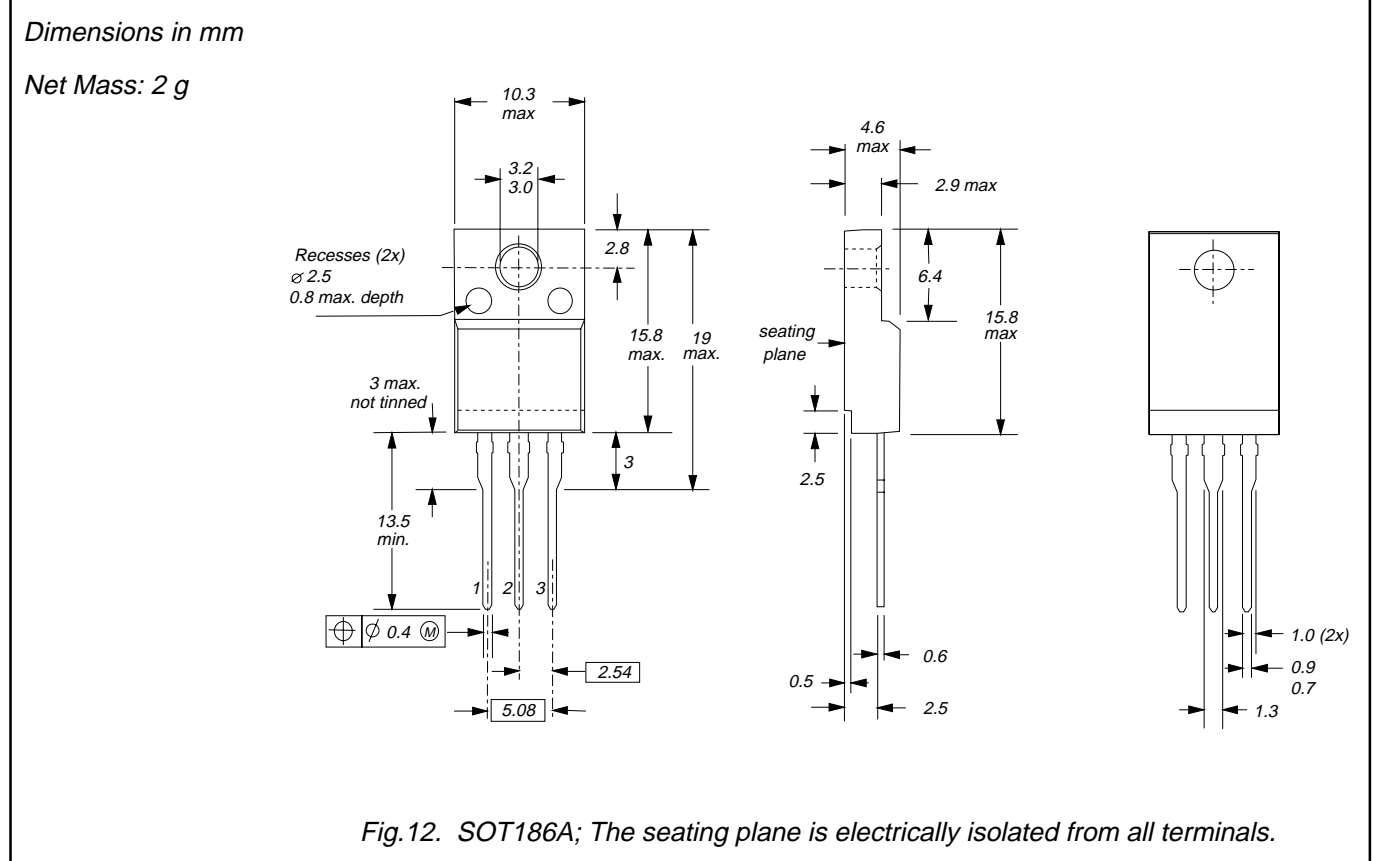
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**MECHANICAL DATA**



**Notes**

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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### DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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